



# Frequency Dependence and Anisotropy of the Glass Transition $T_g$ of $\text{Rb}_{0.52}(\text{ND}_4)_{0.48}\text{D}_2\text{PO}_4$

Authors: J. Stankowski, Z. Trybula, & V. Hugo  
Schmidt

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FREQUENCY DEPENDENCE AND ANISOTROPY OF THE GLASS TRANSITION  
 $T_g$  OF  $Rb_{0.52}(ND_4)_{0.48}D_2PO_4$

J.STANKOWSKI, Z.TRYBUŁA,  
Institute of Molecular Physics, Polish Academy of Sciences,  
Poznań, POLAND  
V.H.SCHMIDT  
Department of Physics, Montana State University Bozeman,  
Montana, U.S.A.

Abstract The frequency dependence of the glass transition temperature  $T_g$  has been calculated from the Vogel-Fulcher law using dielectric data obtained in the  $10^2$  Hz to  $10^{10}$  Hz region. The best fit was obtained with  $\ln f_0 = 29$  and  $T_0 = 38$  K. The anisotropy of  $T_g$  predicted recently by theory has been observed.

EXPERIMENTAL RESULTS AND DISCUSSION

Studies of the frequency-dependent dielectric properties of  $Rb_{0.52}(ND_4)_{0.48}D_2PO_4$  at low frequency were done by Samara and Schmidt<sup>1</sup> and others<sup>2,3</sup>. In this paper we report the real  $\epsilon'$  and imaginary  $\epsilon''$  dielectric permittivity in the X-band microwave region for temperatures from 5 K to 180 K. Typical rounded cusp dependence for  $\epsilon'(T)$  and narrow rounded maximum for  $\epsilon''(T)$  were observed. Treating this maximum as the temperature  $T_g$  of the glass "transition",  $T_g = 86$  K for  $f = 9.3$  GHz when the microwave electric field is parallel to the c-axis of the  $Rb_{0.52}(ND_4)_{0.48}D_2PO_4$  mixed crystal (FIGURE 1).

According to cluster models of proton glass<sup>4</sup>, short range interactions form partly ordered clusters imbedded in the frustrated proton system. The clusters have a mean relaxation time  $\tau$  strongly related to their volume and temperature, and  $\tau$  decreases rapidly with increasing temperature. According to another viewpoint, to be

explained in detail elsewhere<sup>5</sup>, the  $\tau$  distribution is governed by effective diffusion of  $\text{HPO}_4$  and  $\text{H}_3\text{PO}_4$  defects. In either case, the

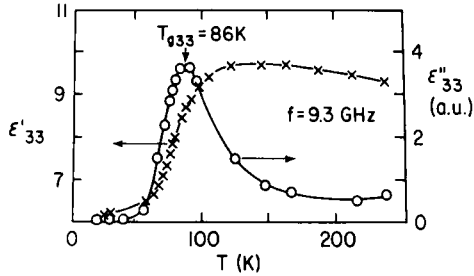


FIGURE 1 Temperature dependences of the real  $\epsilon'_{33}$  and imaginary  $\epsilon''_{33}$  parts of dielectric permittivity of 72% deuterated RADP.

mean  $\tau$  is given by the Vogel-Fulcher law<sup>6</sup> :

$$\tau^{-1} = f_0 \exp(-E/k(T-T_0)), \quad (1)$$

where  $f_0$  and  $T_0$  are scaling parameters and  $E$  is an activation energy. The frequency  $f_0$  is the O-D...O deuteron intrabond transfer attempt frequency, and  $T_0$  should be treated as the temperature below which the O-D...O deuteron system is "frozen". Courtens<sup>2</sup> proposed that Eq.(1) should be modified to the form:

$$\tau^{-1} = f_0 \exp(-E/k(T-T_0)^\alpha). \quad (2)$$

At the temperature giving maximum  $\epsilon''$  we can say that  $\tau^{-1} = f$ , where  $f$  is the measurement frequency and  $T = T_g$ . Then Eq.(2) gives the formula :

$$(\ln f_0 - \ln f)^{-1} = k(T_g - T_0)^\alpha / E. \quad (3)$$

Figure 2 shows the plot of Eq.(2) for  $\alpha=2$ ,  $\ln f_0=29$  and  $T_0=38$  K, using our experimental point and low frequency measurements<sup>1,3</sup> for  $\epsilon''_{33}$ . The good agreement shows that the Eq.(2) form of the Vogel-Fulcher law describes the proton glass system in our crystal. The values of  $\ln f_0$  and  $T_0$  are practically the same as found by Courtens<sup>2</sup>,  $\ln f_0=28.5$  and  $T_0=30$  K for  $\text{Rb}_{0.38}(\text{ND}_4)_{0.62}\text{D}_2\text{PO}_4$ . In terms of physical parameters, these results illustrate the rapid slowing down of dynamic processes with decreasing temperature, and depending on the

model adopted, the increase in cluster size<sup>4</sup> or the increase in defect diffusion path length between creation and annihilation<sup>5</sup>.

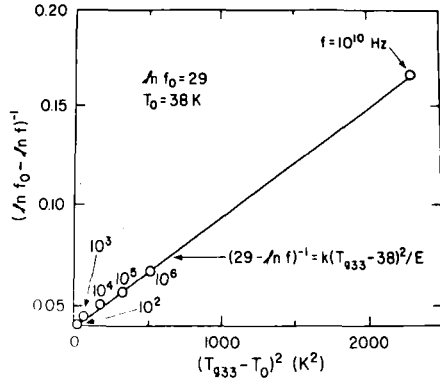


FIGURE 2 A plot of  $(\ln f_0 - \ln f)^{-1}$  vs.  $(T_{g33} - T_0)^2$  for  $\ln f_0 = 29$ ,  $T_0 = 38$  K and  $\alpha = 2$ .

Matsushita and Matsubara<sup>7</sup> (MM) using a cluster theory<sup>4</sup> predicted anisotropy of  $T_g$  - different values of  $T_g$  for susceptibility along the c and a axes. They introduced two order parameters,  $q_x$  and  $q_z$ , which give the temperatures  $T_{g11}$  and  $T_{g33}$ . Figure 3 shows that for  $\text{Rb}_{0.52}(\text{ND}_4)_{0.48}\text{D}_2\text{PO}_4$  the  $\epsilon''$  maxima occur at different temperatures for microwave electric field parallel to the a and c axes. Our data show  $T_{g11} = 82$  K and  $T_{g33} = 86$  K, in accord with MM theory which gives  $T_{g33} > T_{g11}$  for concentration  $x < 0.5$ . Further experiments are planned.

### CONCLUSION

These experiments show that dielectric behavior for proton glasses obeys the Vogel-Fulcher law also when these is isotropic randomness (72 % deuteration) as well as cation randomness (48 %  $\text{ND}_4$ ). In addition, the anisotropy of  $T_g$  predicted by Matsushita and Matsubara<sup>7</sup> was observed.

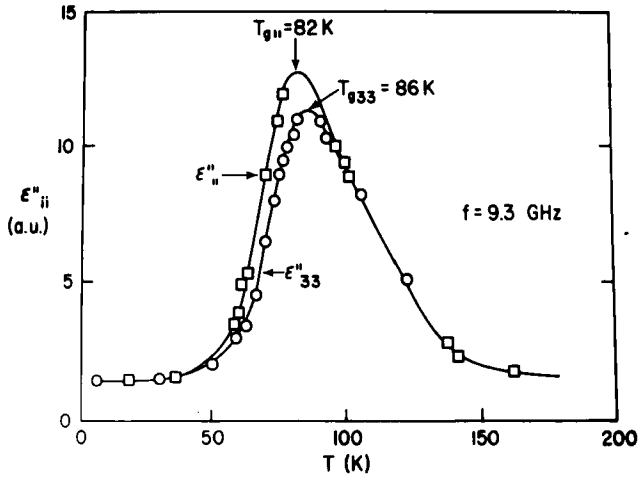


FIGURE 3 Temperature dependences of the imaginary part of electric permittivity in arbitrary units for two orientations of microwave electric field:  $\epsilon''_{33}$  and  $\epsilon''_{11}$ .

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